

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Kok-Weng Loo
Application No. : Not yet available
Confirmation No. : Not yet available
Filed : Concurrently herewith
For : GATE-BODY CROSS-LINK CIRCUITRY FOR
METAL-OXIDE-SEMICONDUCTOR TRANSISTOR
CIRCUITS
Group Art Unit :
Examiner :
Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

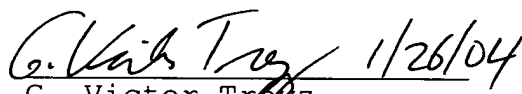
INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97, and 1.98,
applicants hereby bring the attention of the Examiner to the
documents listed on the attached Form PTO-1449 (submitted in
duplicate).

A copy of each listed document is enclosed herewith.

Respectfully submitted,


G. Victor Trezz
Reg. No. 36,294
Attorney for Applicants
Customer No. 36532

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Substitute for form 1449B/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete If Known			
		Application Number			
		Filing Date	Herewith		
		First Named Inventor	Kok-Weng Loo		
		Art Unit			
		Examiner Name			
Sheet	1	of	2	Attorney Docket Number	A1022

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		Andy Wei et al. "Design Methodology for Minimizing Hysteretic Vt -Variation in Partially-Depleted SOI CMOS" (c) 1997 IEEE in IEDM 97 pp. 411-414	
		"SOI Technology: IBM's Next Advance in Chip Design" IBM Corporation (undated)	
		Ghavam G. Shahidi et al. "Partially-Depleted SOI Technology for Digital Logic," 1999 IEEE International Solid-State Circuits Conference, IEEE 1999	
		Jean-Luc Pelloie, "SOI CMOS requires complex modeling http://www.eetimes.com/story/OEG20020923S0060 September 23, 2002, EETIMES	
		Vaughn Betz et al., "Circuit Design, Transistor Sizing and Wire Layout of FPGA Interconnect," IEEE Custom Integrated Circuits Conference, 1999 pp. 1-4	
		Koushik K. Das et al., "Circuit Style Comparison based on the Variable Voltage Transfer Characteristic and floating B Ratio Concept of Partially Depleted SOI" (undated) 9/17/02	
		"CMOS Devices and Reliability - SOD Devices & Circuits (Session 16)" IEDM 1997	
		Alan Joch "Silicon on Insulator", Computerworld 12/18/00	
		"Silicon On Insulator" Technology Article - Deviant PC http://www.deviantpc.com/articles/SOI/index.shtml (4/03)	
		"SOI Circuit Design Concepts" pp 34, 35, and 196-209	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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		Examiner Name	
Sheet	2	of	2
		Attorney Docket Number	A1022

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		Robert Richmond, "Silicon-on-Insulator Technology" www.sysopt.com/articles/soi/index3.html 11/8/00	
		"Silicon on Insulator"; http://www.okisemi.com/jp/english/bt-soi.htm 4/25/03	
		Jacques Gautier et al., "SOI Floating-Body, Device and Circuit Issues", IEDM 1997 pp 407-410	
		J.P. Colinge et al., "Potential of SOI for Analog and Mixed Analog-Digital Low-Power Applications, 1995 IEEE International Solid-State Circuits Conference (IEEE 1995)	
		Carlos Mazure et al., "ICs tailored for exotic substances", EE Times, 9/23/2002	
		Andre Auberton-Herve, "SOI sharpens the leading edge as silicon scales to 90 nanometers", EE Times 9/23/2002	

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